

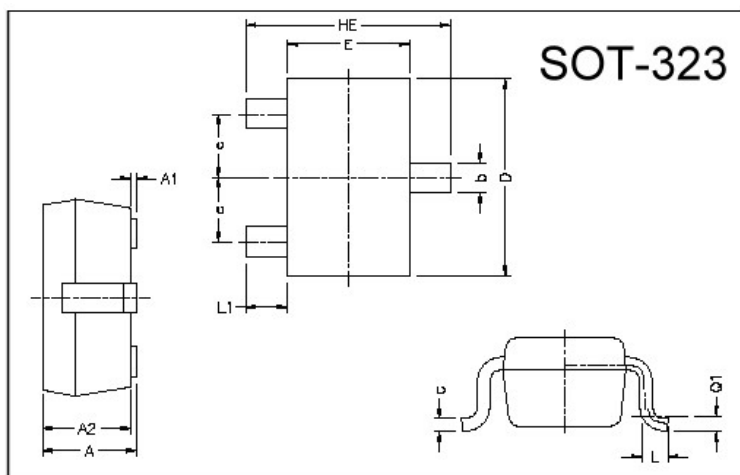
GSMBTA05

NPN SILICON TRANSISTOR

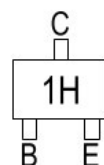
Description

The GSMBTA05 is designed for general purpose amplifier applications.

Package Dimensions



Marking :



REF.	Millimeter		REF.	Millimeter	
	Min.	Max.		Min.	Max.
A	0.80	1.10	L1	0.42 REF.	
A1	0	0.10	L	0.15	0.35
A2	0.80	1.00	b	0.25	0.40
D	1.80	2.20	c	0.10	0.25
E	1.15	1.35	e	0.65 REF.	
HE	1.80	2.40	Q1	0.15 BSC.	

Absolute Maximum Ratings at Ta = 25°C

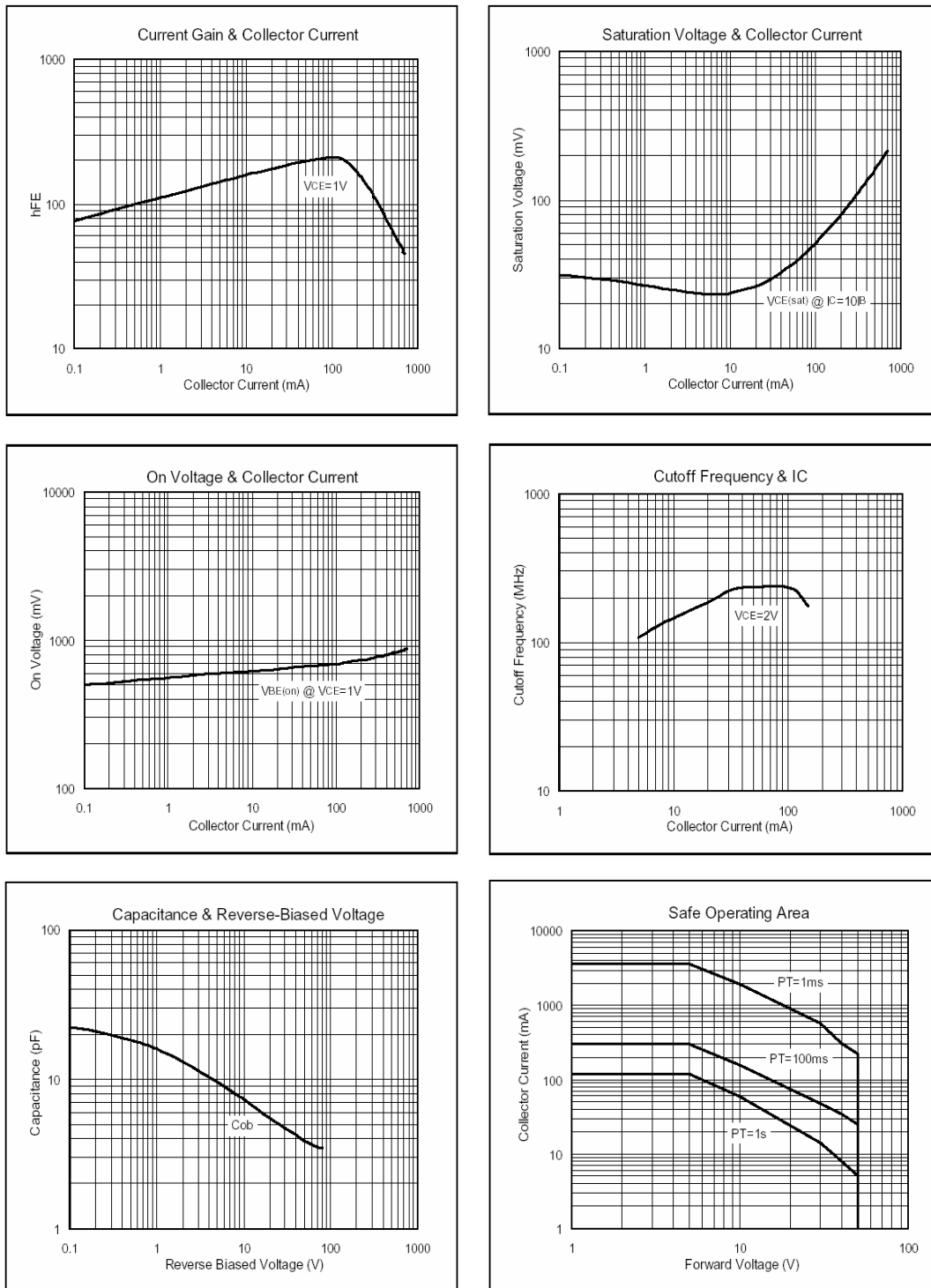
Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	°C
Storage Temperature	Tstg	-55~+150	°C
Collector to Base Voltage	VCBO	60	V
Collector to Emitter Voltage	VCEO	60	V
Emitter to Base Voltage	VEBO	4	V
Collector Current	Ic	500	mA
Total Power Dissipation	Pd	225	mW

Electrical Characteristics (Ta = 25°C, unless otherwise noted)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	60	-	-	V	Ic=100uA, IE=0
BVCEO	60	-	-	V	Ic=1mA, IB=0
BVEBO	4	-	-	V	IE=100uA, Ic=0
ICBO	-	-	100	nA	VCB=60V, IE=0
ICEO	-	-	100	nA	VCE=60V, IB=0
*VCE(sat)	-	-	250	mV	Ic=100mA, IB=10mA
*VBE(on)	-	-	1.2	V	VCE=1V, Ic=100mA
*hFE1	50	-	-		VCE=1V, Ic=10mA
*hFE2	50	-	-		VCE=1V, Ic=100mA
fT	100	-	-	MHz	VCE=2V, Ic=10mA, f=100MHz

* Pulse Test: Pulse Width ≤ 380μs, Duty Cycle ≤ 2%

Characteristics Curve



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Head Office And Factory:

- **Taiwan:** No. 17-1 Tatung Rd. Fu Kou Hsin-Chu Industrial Park, Hsin-Chu, Taiwan, R. O. C.
TEL : 886-3-597-7061 FAX : 886-3-597-9220, 597-0785
- **China:** (201203) No.255, Jang-Jiang Tsai-Lueng RD. , Pu-Dung-Hsin District, Shang-Hai City, China
TEL : 86-21-5895-7671 ~ 4 FAX : 86-21-38950165